



Nanoscale four-point charge transport measurements in topological insulator thin films

Arthur Leis

Information

Band / Volume 70

ISBN 978-3-95806-580-2

Forschungszentrum Jülich GmbH
Peter Grünberg Institut (PGI)
Quantum Nanoscience (PGI-3)

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Schriften des Forschungszentrums Jülich
Reihe Information / Information

Band / Volume 70

ISSN 1866-1777

ISBN 978-3-95806-580-2

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